

600V High and Low Side Driver

PRODUCT SUMMARY

• V_{OFFSET}	600 V max.
• $I_{O+/-}$	2.5A / 3.5A
• V_{OUT}	10 V - 20 V
• $t_{on/off}$ (typ.)	180ns / 200ns

GENERAL DESCRIPTION

The SiLM21814AQ is a high voltage, high speed power MOSFET and IGBT drivers with independent high- and low-side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side configuration which operates up to 600 V.

FEATURES

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Low V_{CC} operation
- Tolerant to negative transient voltage, dV/dt immune
- Gate drive supply range from 10 V to 20 V
- Undervoltage lockout for both channels
- 3.3 V, and 5 V logic compatible
- CMOS Schmitt-triggered inputs with pull-down
- Matched propagation delay for both channels
- Outputs in phase with inputs
- RoHS compliant
- SOP14 package
- AEC-Q 100 qualified for automotive

TYPICAL APPLICATION CIRCUIT

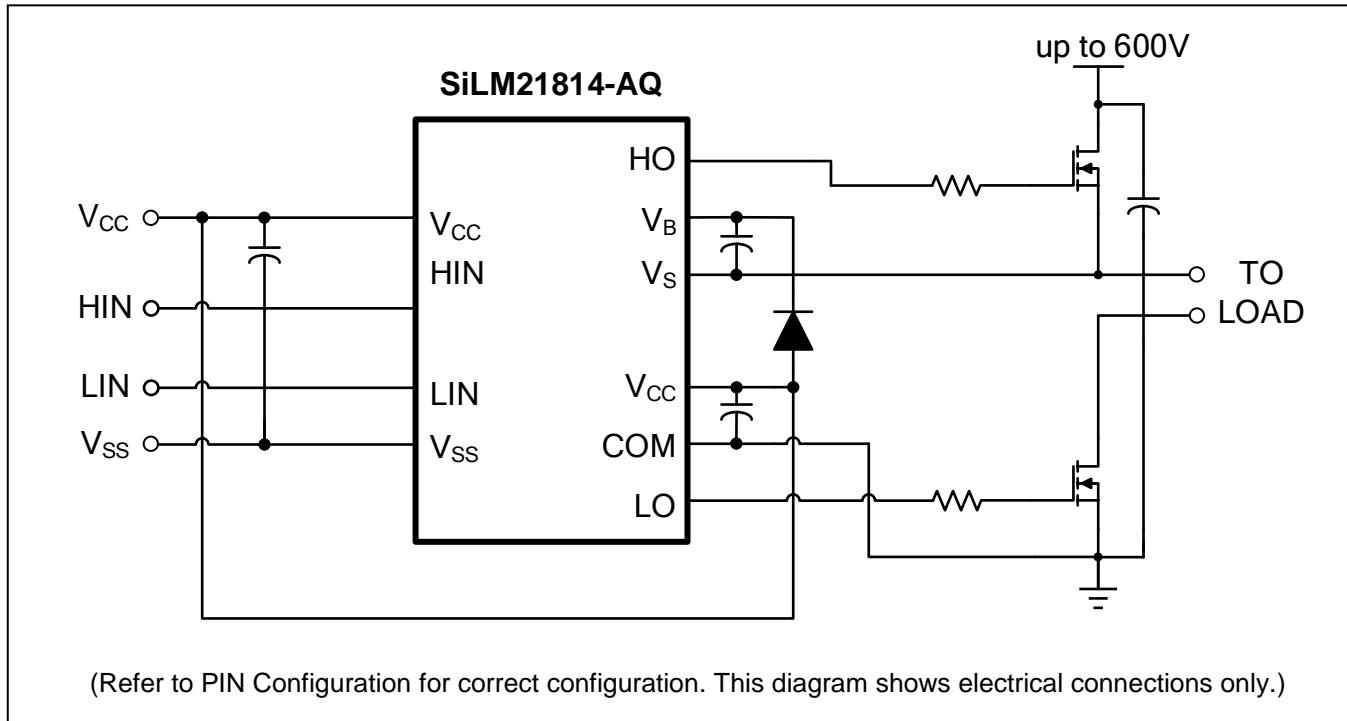


Table of Contents

Product Summary	1
General Description	1
Features	1
Typical Application Circuit	1
PIN Configuration	3
PIN Description	3
Ordering Information	3
Functional Block Diagram	4
Absolute Maximum Ratings	5
Recommended Operation Conditions	5
Dynamic Electrical Characteristics	6
Static Electrical Characteristics	6
Typical Performance Characteristics	8
Package Case Outlines	10
Revision History	11

PIN CONFIGURATION

Package	Pin Configuration (Top View)			
SOP14		1 HIN NC 14	2 LIN V _B 13	3 VSS HO 12
	4 NC V _s 11	5 COM NC 10	6 LO NC 9	7 VCC NC 8

PIN DESCRIPTION

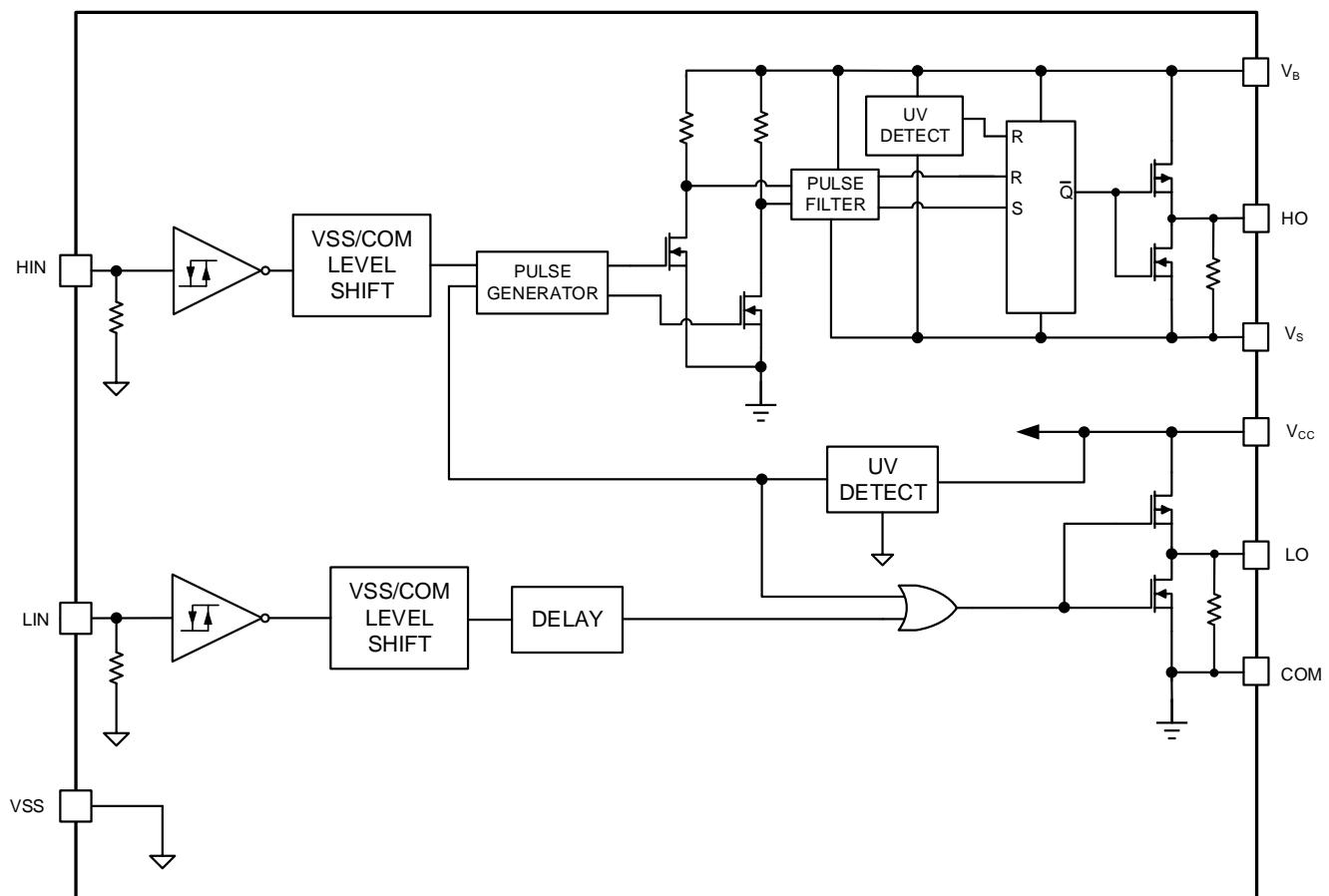
No.	Pin	Description
1	HIN	Logic input for high-side gate driver output (HO), in phase
2	LIN	Logic input for low-side gate driver output (LO), in phase
3	VSS	Logic ground
5	COM	Low-side return
6	LO	Low-side gate drive output
7	Vcc	Low-side and logic fixed supply
11	V _s	High-side floating supply return
12	HO	High-side gate drive output
13	V _B	High-side floating supply
4,8,9,10,14	NC	No Connection

ORDERING INFORMATION

Industrial Range: -40°C to +125°C

Order Part No.	Package	QTY
SiLM21814CJ-AQ	SOP14, Pb-Free	2500/Reel

FUNCTIONAL BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Definition		Min.	Max.	Units
V_B	High-side floating absolute voltage		-0.3	625	V
V_S	High-side floating supply offset voltage		$V_B - 25$	$V_B + 0.3$	
V_{HO}	High-side floating output voltage		$V_S - 0.3$	$V_B + 0.3$	
V_{CC}	Low-side and logic fixed supply voltage		-0.3	25	
V_{LO}	Low-side output voltage		-0.3	$V_{CC} + 0.3$	
V_{IN}	Logic input voltage (HIN & LIN)		$V_{SS}-0.3$	$V_{SS} + V_{CC}$	
V_{SS}	Logic ground		-5	+5	
dV_S/dt	Allowable offset supply voltage transient		---	50	V/ns
P_D	Package power dissipation @ $T_A \leq +25^\circ\text{C}$	SOP14	---	1.0	W
θ_{JA}	Thermal resistance, junction to ambient	SOP14	---	120	$^\circ\text{C}/\text{W}$
T_J	Junction temperature		---	150	$^\circ\text{C}$
T_S	Storage temperature		-55	150	
T_L	Lead temperature (soldering, 10 seconds)		---	300	

Note: Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

RECOMMENDED OPERATION CONDITIONS

Symbol	Definition	Min	Max	Units
V_B	High-side floating absolute voltage	$V_S + 10$	$V_S + 20$	V
V_S	High-side floating supply offset voltage		600	
V_{HO}	High-side floating output voltage	V_S	V_B	
V_{CC}	Low-side and logic fixed supply voltage	10	20	
V_{LO}	Low-side output voltage	0	V_{CC}	
V_{IN}	Logic input voltage (HIN & LIN)	V_{SS}	$V_{SS}+V_{CC}$	
T_A	Ambient temperature	-40	125	$^\circ\text{C}$

Note: For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at a 15 V differential.

DYNAMIC ELECTRICAL CHARACTERISTICS

V_{BIAS} (V_{CC} , V_{BS}) = 15 V, C_L = 1000 pF and $T_A = T_J$ = -40°C~125°C unless otherwise specified.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
t_{on}	Turn-on propagation delay	$V_S = 0 \text{ V}$	---	180	270	ns
t_{off}	Turn-off propagation delay	$V_S = 0 \text{ V}$	---	200	300	
t_r	Turn-on rise time		---	10	20	
t_f	Turn-off fall time		---	8	20	
MT	Delay matching, HS & LS turn-on/off		---	0	35	

STATIC ELECTRICAL CHARACTERISTICS

V_{BIAS} (V_{CC} , V_{BS}) = 15 V, $V_{SS}=\text{COM}$ and $T_A = T_J$ = -40°C~125°C unless otherwise specified. The V_{IN} , V_{TH} , and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the logic input leads: HIN and LIN. The V_o and I_o parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
V_{IH}	Logic "1" input voltage	$V_{CC} = 10 \text{ V to } 20 \text{ V}$	2.5	---	---	V
V_{IL}	Logic "0" input voltage		---	---	0.8	
V_{OH}	High level output voltage, $V_{BIAS} - V_o$	$I_o = 20 \text{ mA}$	---	---	0.2	
V_{OL}	Low level output voltage, V_o		---	0.02	0.15	
I_{LK}	Offset supply leakage current	$V_B = V_S = 600 \text{ V}$	---	---	50	μA
I_{QBS}	Quiescent V_{BS} supply current	$V_{IN} = 0 \text{ V}$	30	65	100	
I_{ACC}	Quiescent V_{CC} supply current		130	270	520	
I_{IN+}	Logic "1" input bias current	$HIN=LIN = 5 \text{ V}$	---	27	40	
I_{IN-}	Logic "0" input bias current	$HIN=LIN = 0 \text{ V}$	---	---	5	
V_{BSUV+}	V_{BS} supply undervoltage positive going threshold		8.0	8.9	9.8	
V_{BSUV-}	V_{BS} supply undervoltage negative going threshold		7.4	8.2	9.0	V
V_{CCUV+}	V_{CC} supply undervoltage positive going threshold		8.0	8.9	9.8	
V_{CCUV-}	V_{CC} supply undervoltage negative going threshold		7.4	8.2	9.0	
I_{O+}	Output high short circuit pulsed current ¹	$V_o = 0 \text{ V}$ $V_{IN} = \text{Logic "1"}$ $PW \leqslant 10 \mu\text{s}$		2.5		A
I_{O-}	Output low short circuit pulsed current ¹	$V_o = 15 \text{ V}$ $V_{IN} = \text{Logic "0"}$ $PW \leqslant 10 \mu\text{s}$		3.5		

1) Values are verified by characterization on bench.

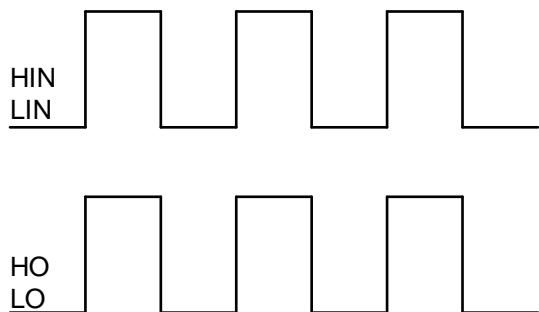


Figure 1. Input/Output Timing Diagram

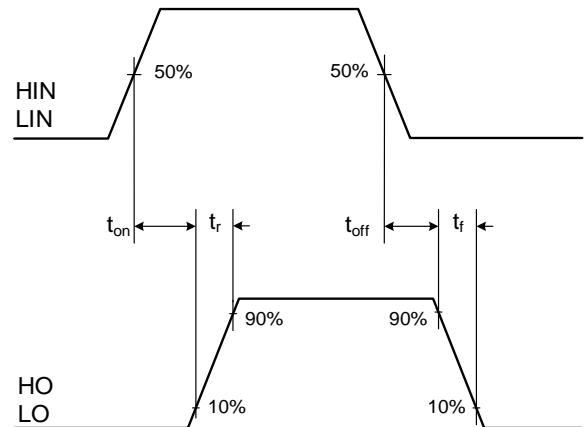


Figure 2. Switching Time Waveform

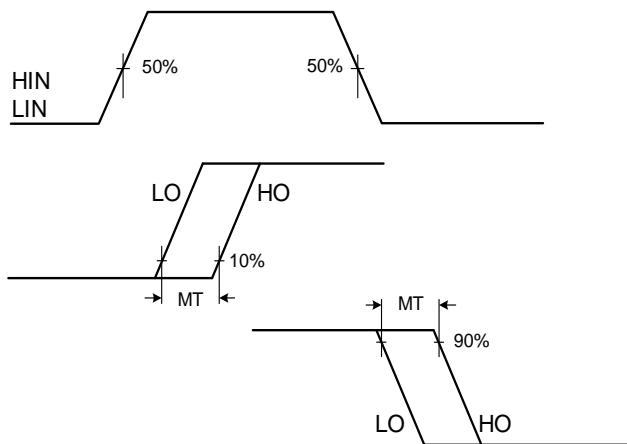


Figure 3. Delay Matching Waveform

TYPICAL PERFORMANCE CHARACTERISTICS

V_{BIAS} (V_{CC} , V_{BS}) = 15 V, $VSS=COM$ and $T_A = 25^\circ C$ unless otherwise specified.

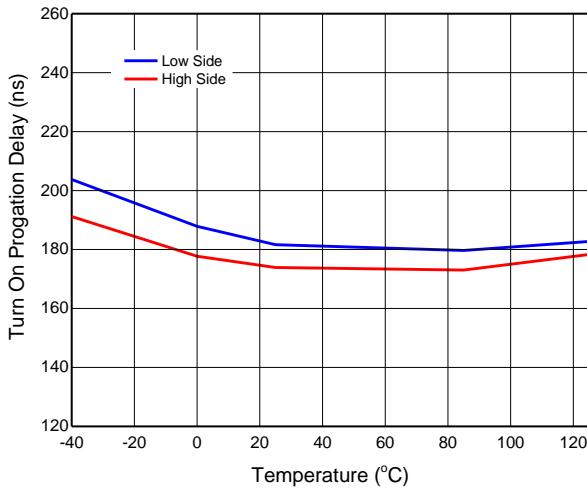


Figure 4. Turn On Delay vs. Temperature

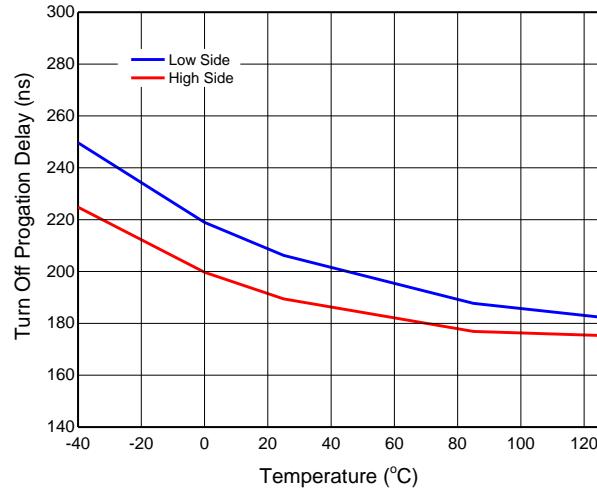


Figure 5. Turn Off Delay vs. Temperature

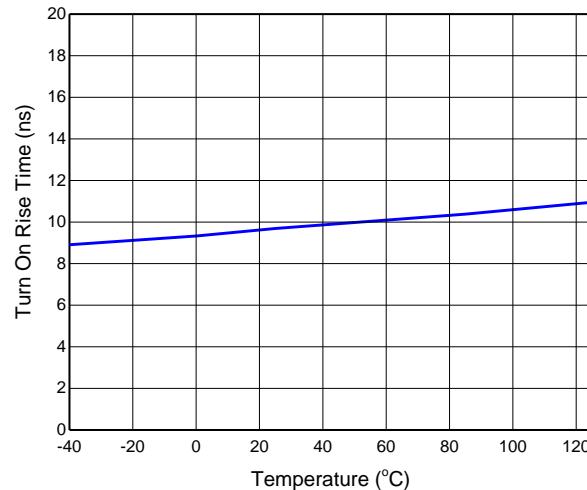


Figure 6. Turn On Rise Time vs. Temperature

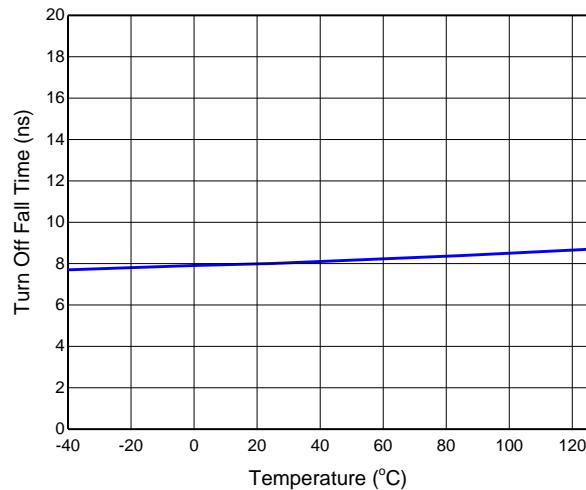


Figure 7. Turn Off Fall Time vs. Temperature

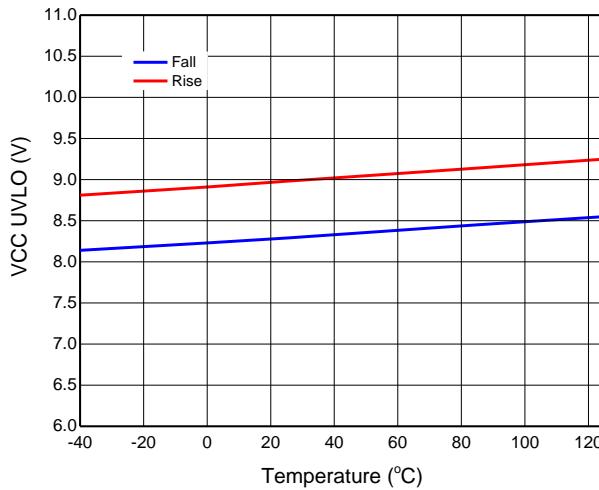


Figure 8. VCC UVLO Threshold vs. Temperature

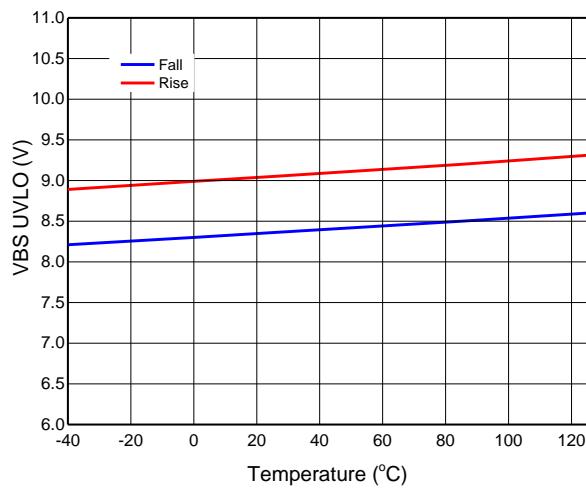


Figure 9. VBS UVLO Threshold vs. Temperature

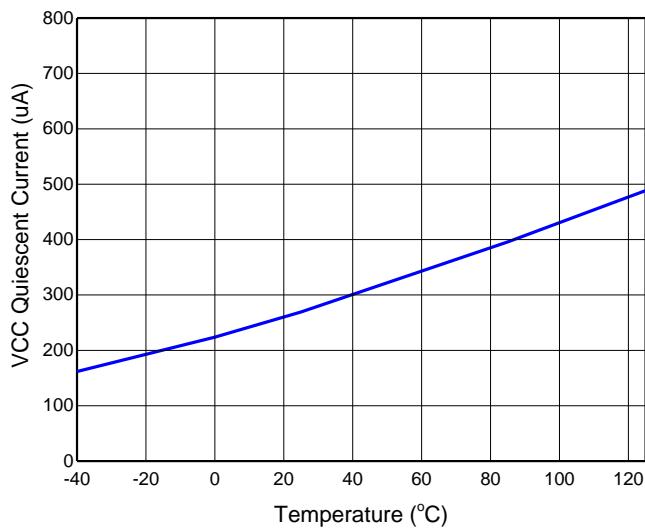


Figure 10. VCC Quiescent Current vs. Temperature

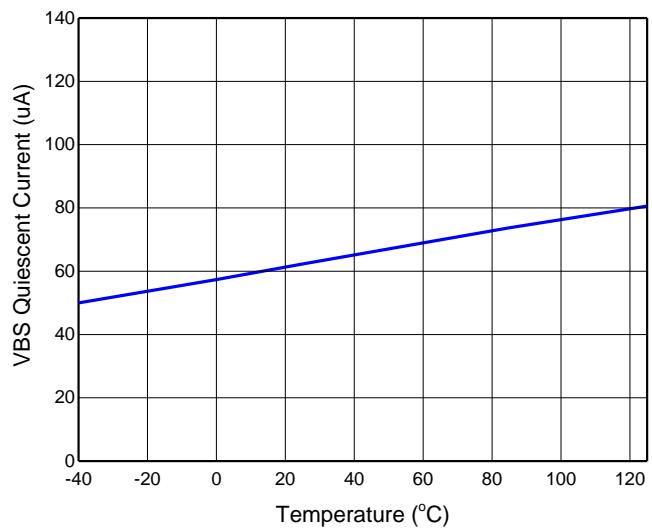


Figure 11. VBS Quiescent Current vs. Temperature

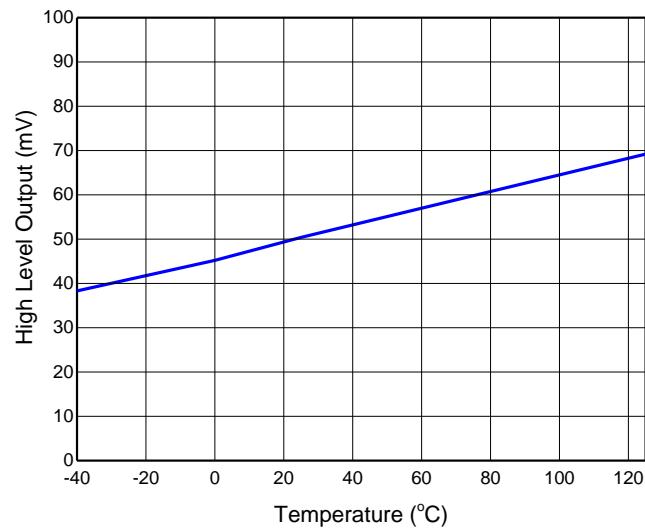


Figure 12. High Level Output vs. Temperature

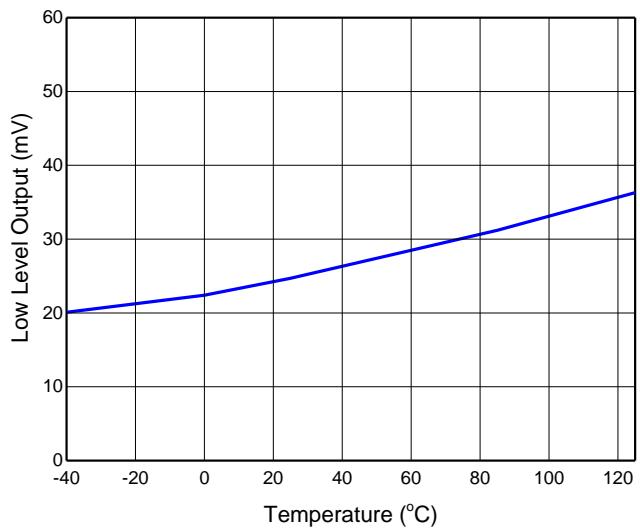


Figure 13. Low Level Output vs. Temperature

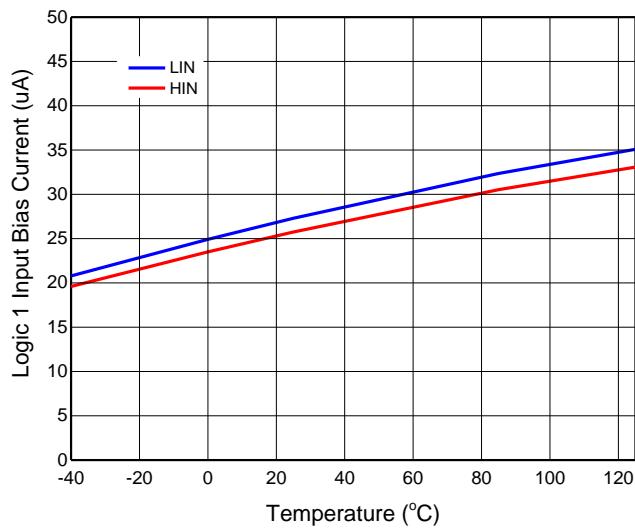
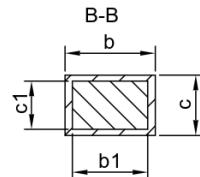
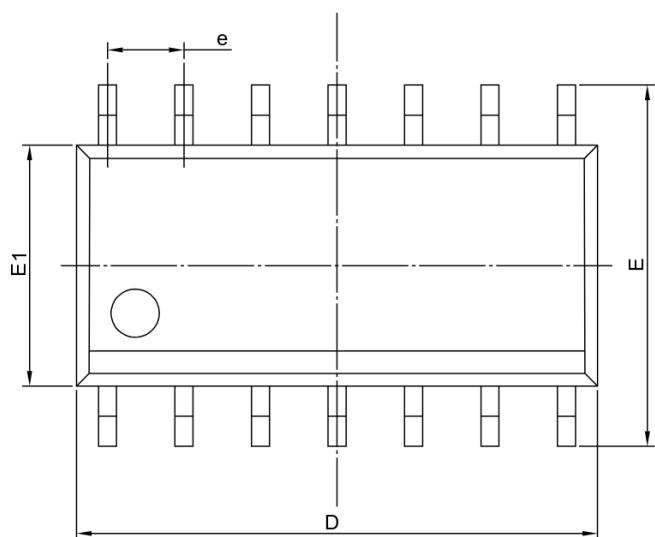
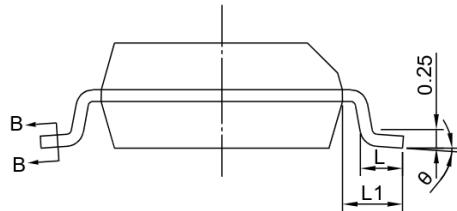
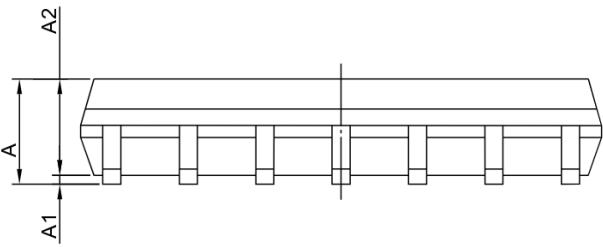


Figure 14. Logic "1" Input Bias Current vs. Temperature

PACKAGE CASE OUTLINES



Dimension	MIN	NOM	MAX
A	-	-	1.75
A1	0.1	-	0.25
A2	1.25	-	-
L	0.4	0.835	1.27
L1	-	1.04	-
θ	0	-	8
b	0.31	-	0.51
b1	0.28	-	0.48
c	0.1	-	0.25
c1	0.1	-	0.25
D	8.45	8.65	8.85
E	5.8	6	6.2
E1	3.8	3.9	4.05
e	1.02	1.27	1.52

Unit : mm

Figure 15. SOP14 Outline Dimensions

REVISION HISTORY

Note: page numbers for previous revisions may differ from page numbers in current version

Page or Item	Subjects (major changes since previous revision)
Rev 1.0 datasheet, 2023-07-04	
Whole document	Rev 1.0: Initial Version Release